



MMBT2222ALP4

40V NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

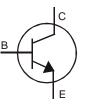
- Low Collector-Emitter Saturation Voltage, V_{CE(sat)}
- Ultra-Small Leadless Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

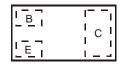
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.0009 grams (Approximate)

X2-DFN1006-3

Bottom View



Device Symbol



Top View Device Schematic

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT2222ALP4-7B	2S	7	8	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

2S = Product Type Marking Code

Bar Denotes Base and Emitter Side

4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



Top View



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current - Continuous	Ic	600	mA
Peak Collector Current	I _{CM}	800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	460	mW
Power Dissipation (Note 6)	PD	1	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	272	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	120	°C/W
Thermal Resistance, Junction to Lead (Note 7)	R _{θJL}	110	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

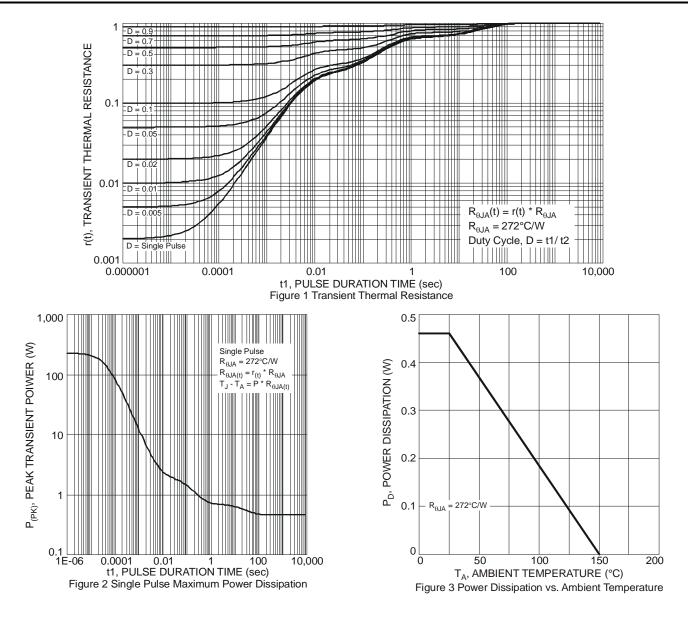
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

Notes: 5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is To a device surface modified of minimum fectommended pad sport 17C4 PCB with single stude 102 copper, in stim measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
 Same as note 5, except device is surface mounted on 25mm X 25mm collector pad heatsink with 102 copper.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





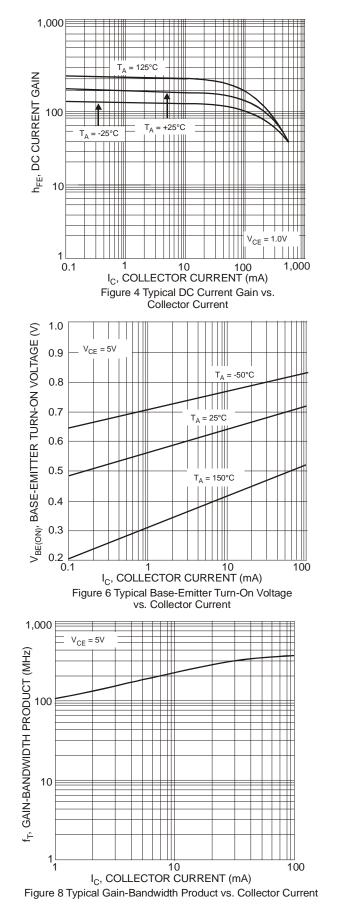
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

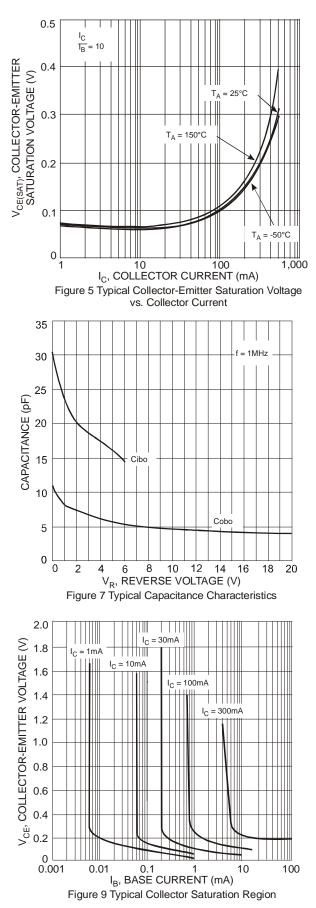
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS						·	
Collector-Base Breakdown Voltage	BV _{CBO}	75		_	V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	40		_	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	6		_	V	$I_{\rm E} = 100 \mu A, I_{\rm C} = 0$	
Collector Cutoff Current	ICEX	_		10	nA	$V_{CE} = 60V, V_{EB(off)} = 3V$	
Collector Cutoff Current		_	_	10	nA	$V_{CB} = 60V, I_E = 0$	
	I _{CBO}	_		10	μΑ	V _{CB} = 60V, I _E = 0, T _A = +125°C	
Emitter Cutoff Current	I _{EBO}	_	_	10	nA	$V_{EB} = 5V, I_{C} = 0$	
Base Cutoff Current	I _{BL}			20	nA	$V_{CE} = 60V, V_{EB(off)} = 3V$	
ON CHARACTERISTICS (Note 6)			-			· · · · · · · · · · · · · · · · · · ·	
		35		_	_	$V_{CE} = 10V, I_{C} = 0.1mA$	
		50				$V_{CE} = 10V, I_{C} = 1mA$	
		75		_	_	$V_{CE} = 10V, I_{C} = 10mA$	
DC Current Gain	h _{FE}	35		_		$V_{CE} = 10V, I_{C} = 10mA, T_{A} = -55^{\circ}C$	
		100		300	_	$V_{CE} = 10V, I_{C} = 150mA$	
		50		_		$V_{CE} = 1V, I_{C} = 150mA$	
		40				$V_{CE} = 10V, I_{C} = 500mA$	
Collector-Emitter Saturation Voltage	N			0.3	V	I _C = 150mA, I _B = 15mA	
	V _{CE(sat)}			1.0		$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$	
Base-Emitter Saturation Voltage	M	0.6		1.2	v	$I_{C} = 150 \text{mA}, I_{B} = 15 \text{mA}$	
	V _{BE(sat)}	—		2.0	v	$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm mA}$	
SMALL SIGNAL CHARACTERISTICS (Note 6)				i	i		
Output Capacitance	C _{obo}	_		8	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$	
Input Capacitance	Cibo			25	pF	$V_{EB} = 0.5V$, f = 1.0MHz, I _C = 0	
Current Gain-Bandwidth Product	f _T	300	—	—	MHz	$V_{CE} = 20V, I_C = 20mA, f = 100MHz$	
Noise Figure	NF	—	—	4.0	dB	$\label{eq:Vce} \begin{split} V_{CE} &= 10V, \ I_C = 100 \mu A, \ R_S = 1.0 k \Omega, \\ f &= 1.0 k Hz \end{split}$	
Input Impedance	h _{ie}	0.25		1.25	kΩ		
Voltage Feedback Ratio	h _{re}		_	4.0	X 10 ⁻⁴		
Small-Signal Current Gain	h _{fe}	75	_	375	_	$I_{C} = 10 \text{mA}, V_{CE} = 10 \text{V}, f = 1.0 \text{kHz}$	
Output Admittance	h _{oe}	25		200	μS]	
SWICHING CHARACTERISTICS (Note 6)						·	
Delay Time	t _d			10		$V_{CC} = 30V, V_{BE(off)} = -0.5V,$	
Rise Time	tr			25	nS	$I_{C} = 150 \text{mA}, I_{B1} = 15 \text{mA}$	
Storage Time	ts			225	115	V _{CC} = 30V, I _C = 150mA,	
Fall Time	t _f			60		$I_{B1} = I_{B2} = 15 \text{mA}$	

Notes: 6. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



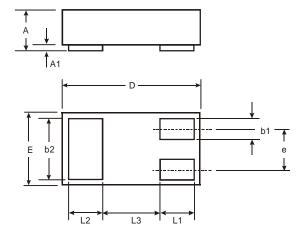
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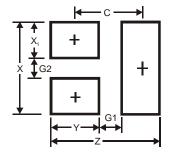


Package Outline Dimensions



X2-DFN1006-3					
Dim	Min	Max	Тур		
Α	-	0.40			
A1	0	0.05	0.03		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
Ш	0.55	0.65	0.60		
e	-		0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3		_	0.40		
All	Dimens	sions in	mm		

Suggested Pad Layout



Dimensions	Value (in mm)		
Z	1.1		
G1	0.3		
G2	0.2		
Х	0.7		
X1	0.25		
Y	0.4		
С	0.7		



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